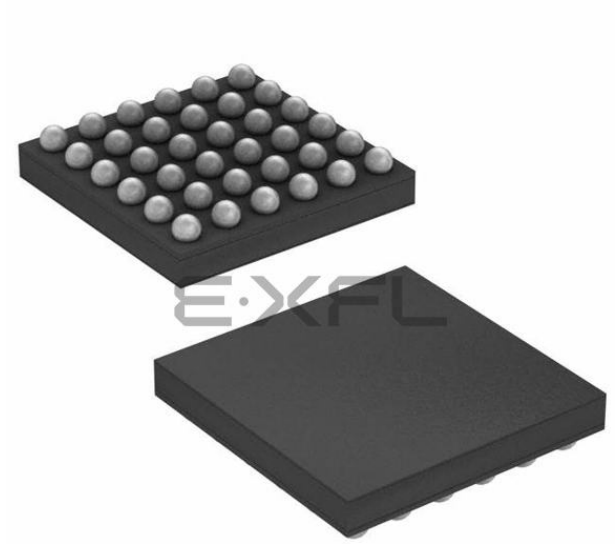

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	29
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	36-UFBGA, WLCSP
Supplier Device Package	36-WLCSP
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f051t8y6tr

List of tables

3.14.2 General-purpose timers (TIM2, 3, 14, 15, 16, 17)

There are six synchronizable general-purpose timers embedded in the STM32F051xx devices (see *Table 7* for differences). Each general-purpose timer can be used to generate PWM outputs, or as simple time base.

TIM2, TIM3

STM32F051xx devices feature two synchronizable 4-channel general-purpose timers. TIM2 is based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. TIM3 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2 and TIM3 general-purpose timers can work together or with the TIM1 advanced-control timer via the Timer Link feature for synchronization or event chaining.

TIM2 and TIM3 both have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Their counters can be frozen in debug mode.

TIM14

This timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM14 features one single channel for input capture/output compare, PWM or one-pulse mode output.

Its counter can be frozen in debug mode.

TIM15, TIM16 and TIM17

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM15 has two independent channels, whereas TIM16 and TIM17 feature one single channel for input capture/output compare, PWM or one-pulse mode output.

The TIM15, TIM16 and TIM17 timers can work together, and TIM15 can also operate withTIM1 via the Timer Link feature for synchronization or event chaining.

TIM15 can be synchronized with TIM16 and TIM17.

TIM15, TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation.

Their counters can be frozen in debug mode.

3.14.3 Basic timer TIM6

This timer is mainly used for DAC trigger generation. It can also be used as a generic 16-bit time base.

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It

Table 13. Pin definitions (continued)

Pin number						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	UFBGA64	LQFP48/UFQFPN48	WLCSP36	LQFP32	UFQFPN32					Alternate functions	Additional functions
33	H8	25	-	-	-	PB12	I/O	FT	(5)	SPI2_NSS, TIM1_BKIN, TSC_G6_IO2, EVENTOUT	-
34	G8	26	-	-	-	PB13	I/O	FT	(5)	SPI2_SCK, TIM1_CH1N, TSC_G6_IO3	-
35	F8	27	-	-	-	PB14	I/O	FT	(5)	SPI2_MISO, TIM1_CH2N, TIM15_CH1, TSC_G6_IO4	-
36	F7	28	-	-	-	PB15	I/O	FT	(5)	SPI2_MOSI, TIM1_CH3N, TIM15_CH1N, TIM15_CH2	RTC_REFIN
37	F6	-	-	-	-	PC6	I/O	FT	-	TIM3_CH1	-
38	E7	-	-	-	-	PC7	I/O	FT	-	TIM3_CH2	-
39	E8	-	-	-	-	PC8	I/O	FT	-	TIM3_CH3	-
40	D8	-	-	-	-	PC9	I/O	FT	-	TIM3_CH4	-
41	D7	29	E2	18	18	PA8	I/O	FT	-	USART1_CK, TIM1_CH1, EVENTOUT, MCO	-
42	C7	30	D1	19	19	PA9	I/O	FT	-	USART1_TX, TIM1_CH2, TIM15_BKIN, TSC_G4_IO1	-
43	C6	31	C1	20	20	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, TIM17_BKIN, TSC_G4_IO2	-
44	C8	32	C2	21	21	PA11	I/O	FT	-	USART1_CTS, TIM1_CH4, COMP1_OUT, TSC_G4_IO3, EVENTOUT	-

5 Memory mapping

To the difference of STM32F051x8 memory map in *Figure 10*, the two bottom code memory spaces of STM32F051x4/STM32F051x6 end at 0x0000 3FFF/0x0000 7FFF and 0x0800 3FFF/0x0000 7FFF, respectively.

Figure 10. STM32F051x8 memory map

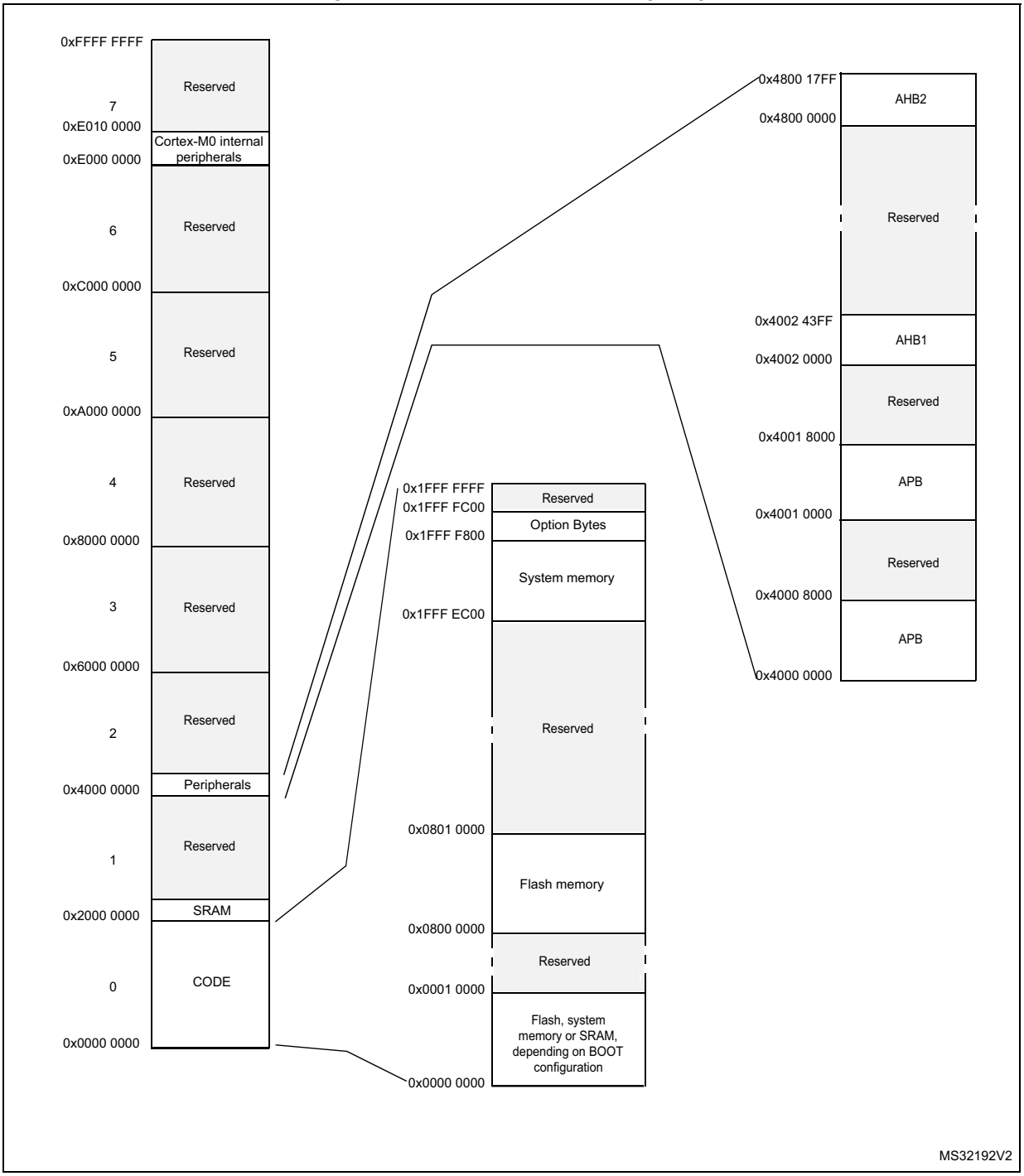


Table 16. STM32F051xx peripheral register boundary addresses

Bus	Boundary address	Size	Peripheral
	0x4800 1800 - 0x5FFF FFFF	~384 MB	Reserved
AHB2	0x4800 1400 - 0x4800 17FF	1 KB	GPIOF
	0x4800 1000 - 0x4800 13FF	1 KB	Reserved
	0x4800 0C00 - 0x4800 0FFF	1 KB	GPIOD
	0x4800 0800 - 0x4800 0BFF	1 KB	GPIOC
	0x4800 0400 - 0x4800 07FF	1 KB	GPIOB
	0x4800 0000 - 0x4800 03FF	1 KB	GPIOA
	0x4002 4400 - 0x47FF FFFF	~128 MB	Reserved
AHB1	0x4002 4000 - 0x4002 43FF	1 KB	TSC
	0x4002 3400 - 0x4002 3FFF	3 KB	Reserved
	0x4002 3000 - 0x4002 33FF	1 KB	CRC
	0x4002 2400 - 0x4002 2FFF	3 KB	Reserved
	0x4002 2000 - 0x4002 23FF	1 KB	Flash memory interface
	0x4002 1400 - 0x4002 1FFF	3 KB	Reserved
	0x4002 1000 - 0x4002 13FF	1 KB	RCC
	0x4002 0400 - 0x4002 0FFF	3 KB	Reserved
	0x4002 0000 - 0x4002 03FF	1 KB	DMA
	0x4001 8000 - 0x4001 FFFF	32 KB	Reserved
APB	0x4001 5C00 - 0x4001 7FFF	9 KB	Reserved
	0x4001 5800 - 0x4001 5BFF	1 KB	DBGMCU
	0x4001 4C00 - 0x4001 57FF	3 KB	Reserved
	0x4001 4800 - 0x4001 4BFF	1 KB	TIM17
	0x4001 4400 - 0x4001 47FF	1 KB	TIM16
	0x4001 4000 - 0x4001 43FF	1 KB	TIM15
	0x4001 3C00 - 0x4001 3FFF	1 KB	Reserved
	0x4001 3800 - 0x4001 3BFF	1 KB	USART1
	0x4001 3400 - 0x4001 37FF	1 KB	Reserved
	0x4001 3000 - 0x4001 33FF	1 KB	SPI1/I2S1
	0x4001 2C00 - 0x4001 2FFF	1 KB	TIM1
	0x4001 2800 - 0x4001 2BFF	1 KB	Reserved
	0x4001 2400 - 0x4001 27FF	1 KB	ADC
	0x4001 0800 - 0x4001 23FF	7 KB	Reserved
	0x4001 0400 - 0x4001 07FF	1 KB	EXTI
	0x4001 0000 - 0x4001 03FF	1 KB	SYSCFG + COMP
	0x4000 8000 - 0x4000 FFFF	32 KB	Reserved

Table 18. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all VDD power lines (source)(1)	120	mA
ΣI_{VSS}	Total current out of sum of all VSS ground lines (sink)(1)	-120	
$I_{VDD(PIN)}$	Maximum current into each VDD power pin (source)(1)	100	
$I_{VSS(PIN)}$	Maximum current out of each VSS ground pin (sink)(1)	-100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin	25	
	Output current source by any I/O and control pin	-25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins(2)	80	
	Total output current sourced by sum of all I/Os and control pins(2)	-80	
$I_{INJ(PIN)}$(3)	Injected current on B, FT and FTf pins	-5/+0(4)	
	Injected current on TC and RST pin	± 5	
	Injected current on TTa pins(5)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(6)	± 25	

1. All main power (VDD, VDDA) and ground (VSS, VSSA) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
3. A positive injection is induced by $V_{IN} > V_{DDIOx}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 17: Voltage characteristics* for the maximum allowed input voltage values.
4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
5. On these I/Os, a positive injection is induced by $V_{IN} > V_{DDA}$. Negative injection disturbs the analog performance of the device. See note (2) below *Table 54: ADC accuracy*.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 19. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 23. Programmable voltage detector characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD6}	PVD threshold 6	Rising edge	2.66	2.78	2.9	V
		Falling edge	2.56	2.68	2.8	V
V_{PVD7}	PVD threshold 7	Rising edge	2.76	2.88	3	V
		Falling edge	2.66	2.78	2.9	V
$V_{PVDhyst}$(1)	PVD hysteresis	-	-	100	-	mV
$I_{DD(PVD)}$	PVD current consumption	-	-	0.15	0.26(1)	µA

1. Guaranteed by design, not tested in production.

6.3.4 Embedded reference voltage

The parameters given in *Table 24* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 20: General operating conditions*.

Table 24. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.2	1.23	1.25	V
t_{START}	ADC_IN17 buffer startup time	-	-	-	10(1)	µs
$t_{S\_vrefint}$	ADC sampling time when reading the internal reference voltage	-	4(1)	-	-	µs
ΔV_{REFINT}	Internal reference voltage spread over the temperature range	V_{DDA} = 3 V	-	-	10(1)	mV
T_{Coeff}	Temperature coefficient	-	- 100(1)	-	100(1)	ppm/°C

1. Guaranteed by design, not tested in production.

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in *Figure 14: Current consumption measurement scheme*.

All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to CoreMark code.

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency:
  - 0 wait state and Prefetch OFF from 0 to 24 MHz
  - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled $f_{PCLK} = f_{HCLK}$

The parameters given in *Table 25* to *Table 31* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 20: General operating conditions*.

Table 25. Typical and maximum current consumption from V_{DD} at 3.6 V

Symbol	Parameter	Conditions	f_{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ	Max @ T_A(1)			Typ	Max @ T_A(1)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DD}	Supply current in Run mode, code executing from Flash memory	HSE bypass, PLL on	48 MHz	22.0	22.8	22.8	23.8	11.8	12.7	12.7	13.3	mA
			32 MHz	15.0	15.5	15.5	16.0	7.6	8.7	8.7	9.0	
			24 MHz	12.2	13.2	13.2	13.6	7.2	7.9	7.9	8.1	
		HSE bypass, PLL off	8 MHz	4.4	5.2	5.2	5.4	2.7	2.9	2.9	3.0	
			1 MHz	1.0	1.3	1.3	1.4	0.7	0.9	0.9	0.9	
		HSI clock, PLL on	48 MHz	22.0	22.8	22.8	23.8	11.8	12.7	12.7	13.3	
			32 MHz	15.0	15.5	15.5	16.0	7.6	8.7	8.7	9.0	
			24 MHz	12.2	13.2	13.2	13.6	7.2	7.9	7.9	8.1	
		HSI clock, PLL off	8 MHz	4.4	5.2	5.2	5.4	2.7	2.9	2.9	3.0	
	Supply current in Run mode, code executing from RAM	HSE bypass, PLL on	48 MHz	22.2	23.2(2)	23.2	24.4(2)	12.0	12.7(2)	12.7	13.3(2)	
			32 MHz	15.4	16.3	16.3	16.8	7.8	8.7	8.7	9.0	
			24 MHz	11.2	12.2	12.2	12.8	6.2	7.9	7.9	8.1	
		HSE bypass, PLL off	8 MHz	4.0	4.5	4.5	4.7	1.9	2.9	2.9	3.0	
			1 MHz	0.6	0.8	0.8	0.9	0.3	0.6	0.6	0.7	
		HSI clock, PLL on	48 MHz	22.2	23.2	23.2	24.4	12.0	12.7	12.7	13.3	
			32 MHz	15.4	16.3	16.3	16.8	7.8	8.7	8.7	9.0	
			24 MHz	11.2	12.2	12.2	12.8	6.2	7.9	7.9	8.1	
		HSI clock, PLL off	8 MHz	4.0	4.5	4.5	4.7	1.9	2.9	2.9	3.0	

Table 42. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycle
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Year
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycle(2) at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 43*. They are based on the EMS levels and classes defined in application note AN1709.

Table 43. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_A = +25 °C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_A = +25°C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Table 47. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	–0	NA	mA
	Injected current on PA10, PA12, PB4, PB5, PB10, PB15 and PD2 pins with induced leakage current on adjacent pins less than –10 µA	–5	NA	
	Injected current on all other FT and FTf pins	–5	NA	
	Injected current on PA6 and PC0	–0	+5	
	Injected current on all other TTa, TC and RST pins	–5	+5	

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 48* are derived from tests performed under the conditions summarized in *Table 20: General operating conditions*. All I/Os are designed as CMOS- and TTL-compliant (except BOOT0).

Table 48. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Low level input voltage	TC and TTa I/O	-	-	$0.3\ V_{DDIOx}+0.07$(1)	V
		FT and FTf I/O	-	-	$0.475\ V_{DDIOx}-0.2$(1)	
		BOOT0	-	-	$0.3\ V_{DDIOx}-0.3$(1)	
		All I/Os except BOOT0 pin	-	-	$0.3\ V_{DDIOx}$	
V_{IH}	High level input voltage	TC and TTa I/O	$0.445\ V_{DDIOx}+0.398$(1)	-	-	V
		FT and FTf I/O	$0.5\ V_{DDIOx}+0.2$(1)	-	-	
		BOOT0	$0.2\ V_{DDIOx}+0.95$(1)	-	-	
		All I/Os except BOOT0 pin	$0.7\ V_{DDIOx}$	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200(1)	-	mV
		FT and FTf I/O	-	100(1)	-	
		BOOT0	-	300(1)	-	

Input/output AC characteristics

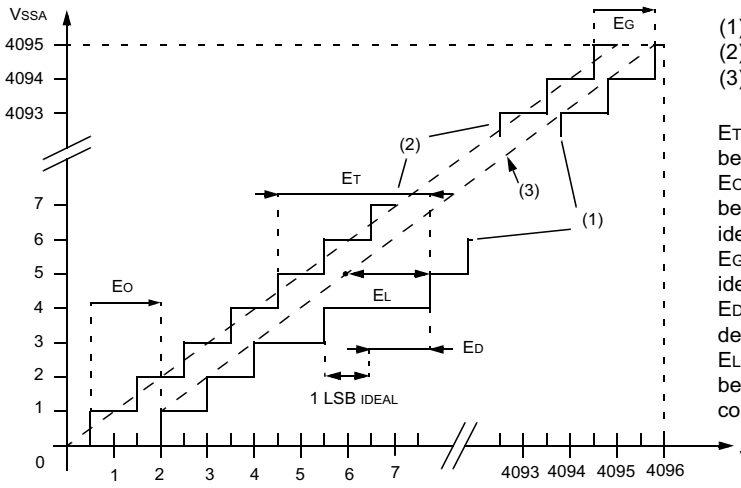
The definition and values of input/output AC characteristics are given in *Figure 23* and *Table 50*, respectively. Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 20: General operating conditions*.

Table 50. I/O AC characteristics(1)(2)

OSPEEDRy [1:0] value(1)	Symbol	Parameter	Conditions	Min	Max	Unit
x0	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF	-	2	MHz
	$t_{f(IO)out}$	Output fall time		-	125	ns
	$t_{r(IO)out}$	Output rise time		-	125	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF	-	10	MHz
	$t_{f(IO)out}$	Output fall time		-	25	ns
	$t_{r(IO)out}$	Output rise time		-	25	
11	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, $V_{DDIOx} \geq$ 2.7 V	-	50	MHz
			C_L = 50 pF, $V_{DDIOx} \geq$ 2.7 V	-	30	
			C_L = 50 pF, V_{DDIOx} < 2.7 V	-	20	
	$t_{f(IO)out}$	Output fall time	C_L = 30 pF, $V_{DDIOx} \geq$ 2.7 V	-	5	ns
			C_L = 50 pF, $V_{DDIOx} \geq$ 2.7 V	-	8	
			C_L = 50 pF, V_{DDIOx} < 2.7 V	-	12	
	$t_{r(IO)out}$	Output rise time	C_L = 30 pF, $V_{DDIOx} \geq$ 2.7 V	-	5	
			C_L = 50 pF, $V_{DDIOx} \geq$ 2.7 V	-	8	
			C_L = 50 pF, V_{DDIOx} < 2.7 V	-	12	
Fm+ configuration (4)	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF	-	2	MHz
	$t_{f(IO)out}$	Output fall time		-	12	ns
	$t_{r(IO)out}$	Output rise time		-	34	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	10	-	ns

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32F0xxxx RM0091 reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design, not tested in production.
3. The maximum frequency is defined in *Figure 23*.
4. When Fm+ configuration is set, the I/O speed control is bypassed. Refer to the STM32F0xxxx reference manual RM0091 for a detailed description of Fm+ I/O configuration.

Figure 25. ADC accuracy characteristics

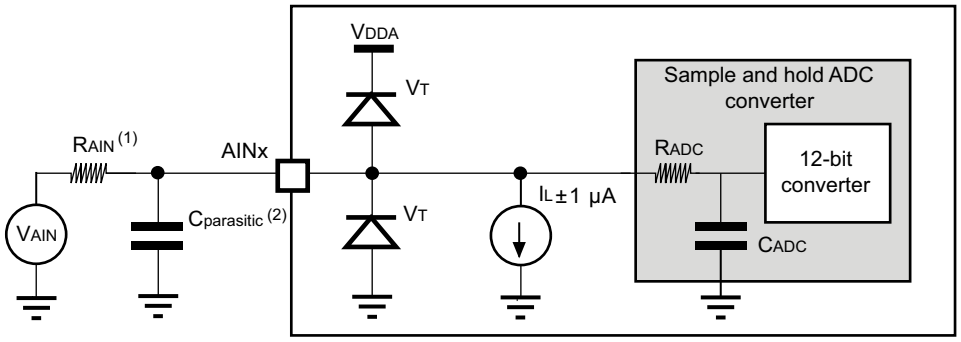


(1) Example of an actual transfer curve
(2) The ideal transfer curve
(3) End point correlation line

E_T = Total Unajusted Error: maximum deviation between the actual and ideal transfer curves.
E_O = Offset Error: maximum deviation between the first actual transition and the first ideal one.
E_G = Gain Error: deviation between the last ideal transition and the last actual one.
E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal ones.
E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

MS19880V2

Figure 26. Typical connection diagram using the ADC



MS33900V2

1. Refer to *Table 52: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 13: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.19 Temperature sensor characteristics

Table 57. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L (1)	V_{SENSE} linearity with temperature	-	± 1	± 2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{30}	Voltage at 30 °C (± 5 °C)(2)	1.34	1.43	1.52	V
t_{START} (1)	ADC_IN16 buffer startup time	-	-	10	µs
t_{S_temp} (1)	ADC sampling time when reading the temperature	4	-	-	µs

1. Guaranteed by design, not tested in production.
2. Measured at V_{DDA} = 3.3 V ± 10 mV. The V_{30} ADC conversion result is stored in the TS_CAL1 byte. Refer to *Table 3: Temperature sensor calibration values*.

6.3.20 V_{BAT} monitoring characteristics

Table 58. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	2 x 50	-	kΩ
Q	Ratio on V_{BAT} measurement	-	2	-	-
Er(1)	Error on Q	–1	-	+1	%
t_{S_vbat} (1)	ADC sampling time when reading the V_{BAT}	4	-	-	µs

1. Guaranteed by design, not tested in production.

6.3.21 Timer characteristics

The parameters given in the following tables are guaranteed by design.

Refer to *Section 6.3.14: I/O port characteristics* for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 59. TIMx characteristics

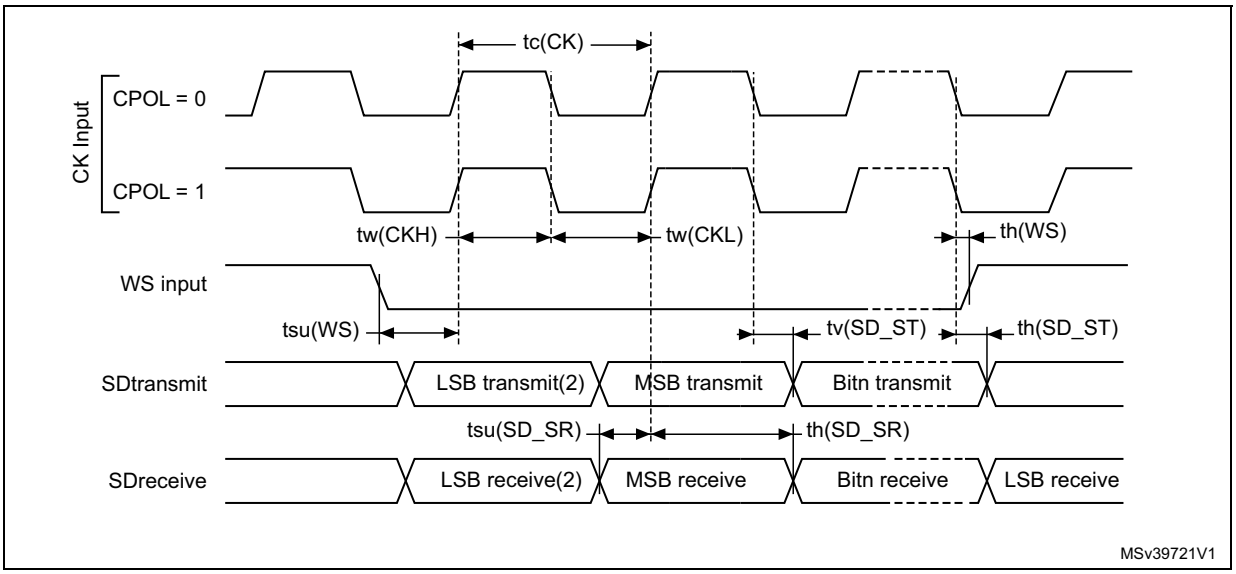
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{res(TIM)}$	Timer resolution time	-	-	1	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	20.8	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	-	-	$f_{TIMxCLK}/2$	-	MHz
		$f_{TIMxCLK}$ = 48 MHz	-	24	-	MHz
t_{MAX_COUNT}	16-bit timer maximum period	-	-	2^{16}	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	1365	-	µs
	32-bit counter maximum period	-	-	2^{32}	-	$t_{TIMxCLK}$
		$f_{TIMxCLK}$ = 48 MHz	-	89.48	-	s

Table 64. I^2S characteristics(1) (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{su(SD\_MR)}$	Data input setup time	Master receiver	6	-	ns
$t_{su(SD\_SR)}$		Slave receiver	2	-	
$t_{h(SD\_MR)}$(2)	Data input hold time	Master receiver	4	-	
$t_{h(SD\_SR)}$(2)		Slave receiver	0.5	-	
$t_{v(SD\_MT)}$(2)	Data output valid time	Master transmitter	-	4	
$t_{v(SD\_ST)}$(2)		Slave transmitter	-	20	
$t_{h(SD\_MT)}$	Data output hold time	Master transmitter	0	-	
$t_{h(SD\_ST)}$		Slave transmitter	13	-	

1. Data based on design simulation and/or characterization results, not tested in production.
2. Depends on f_{PCLK}. For example, if f_{PCLK} = 8 MHz, then T_{PCLK} = 1/f_{PLCLK} = 125 ns.

Figure 32. I^2S slave timing diagram (Philips protocol)



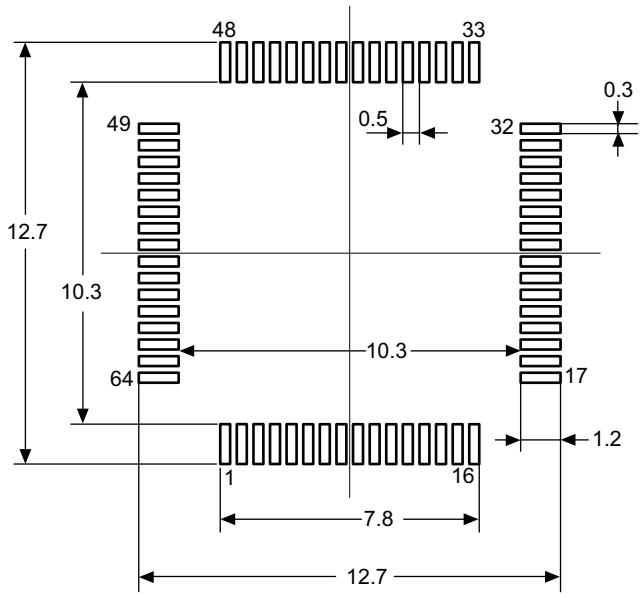
1. Measurement points are done at CMOS levels: 0.3 × V_{DDIOx} and 0.7 × V_{DDIOx}.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Table 67. LQFP64 package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 38. Recommended footprint for LQFP64 package

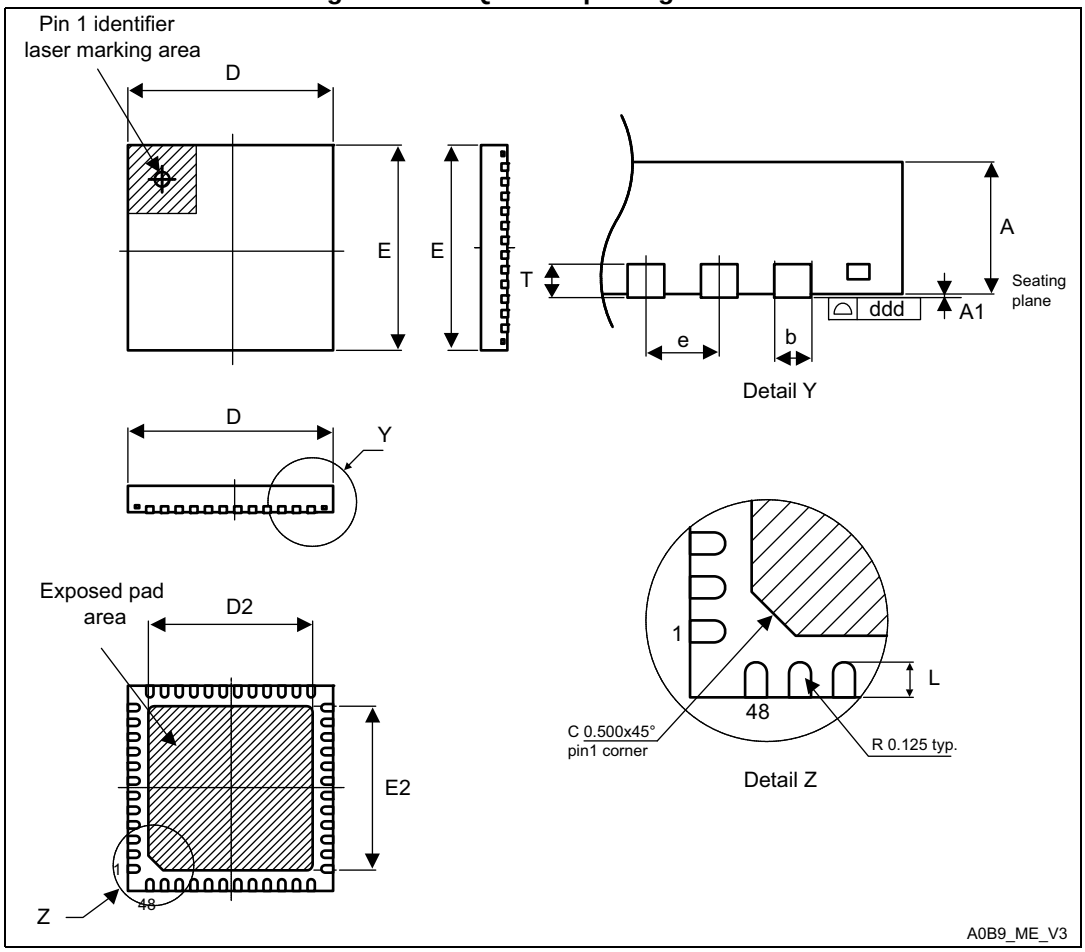


1. Dimensions are expressed in millimeters.

7.4 UFQFPN48 package information

UFQFPN48 is a 48-lead, 7x7 mm, 0.5 mm pitch, ultra-thin fine-pitch quad flat package.

Figure 43. UFQFPN48 package outline



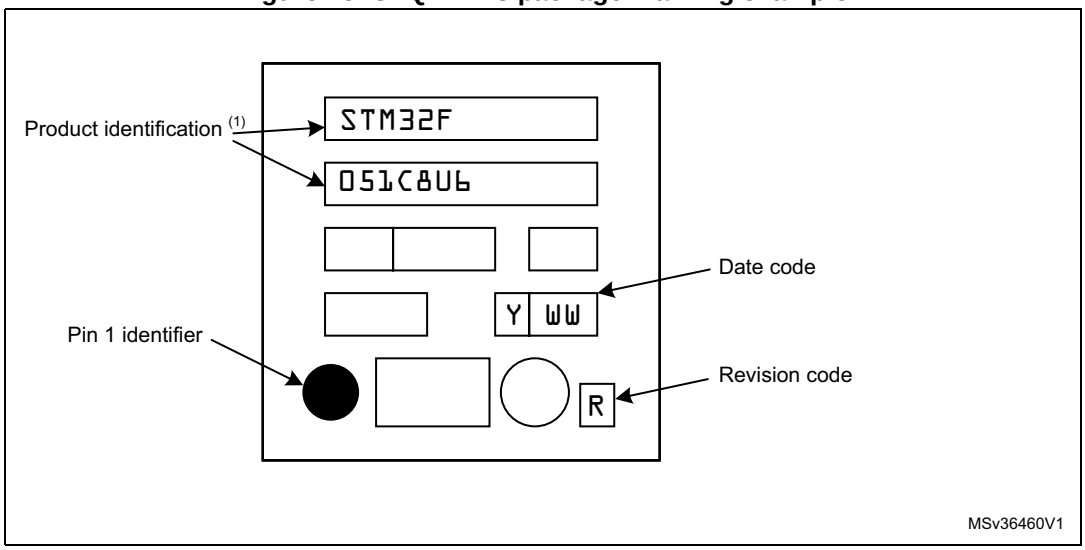
1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. It is recommended to connect and solder this back-side pad to PCB ground.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 45. UFQFPN48 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Using the values obtained in *Table 74* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 100 °C + (45 °C/W × 134 mW) = 100 °C + 6.03 °C = 106.03 °C

This is above the range of the suffix 6 version parts (–40 < T_J < 105 °C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Section 8: Ordering information*) unless we reduce the power dissipation in order to be able to use suffix 6 parts.

Refer to *Figure 55* to select the required temperature range (suffix 6 or 7) according to your ambient temperature or power requirements.

Figure 55. LQFP64 P_D max versus T_A